

Radial Junction Thin Film Solar Cells on VLS-grown Si Nanowires

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Radial junction thin-film solar cells grown over silicon nanowires (SiNWs) offer an opportunity to decouple the path of light absorption and carrier separation. Combining advanced radial junction designs with mature Si thin-film deposition techniques represents a promising road towards a new generation of high performance thin film photovoltaics. High throughputs of SiNWs can be produced via a vapor-liquid-solid (VLS) method. In order to produce SiNWs matrix at a relatively low temperature, we work on a group of low-melting-point alternative catalysts, including indium (In), tin (Sn), and bismuth (Bi) to catalyze SiNW growth in a PECVD system on glass substrates. These catalysts introduce only shallow levels in c-Si and show evidence of removal from the SiNWs by in situ hydrogen plasma treatment. Based on these technologies, we have been able to demonstrate an **8.2% conversion efficiency** and showcased an effective catalyst-doping in the SiNWs core for radial junction cell fabrication.

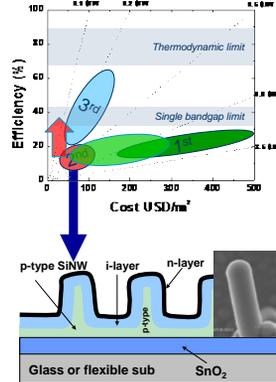
Why Radial Junction (RJ) Photovoltaics?

❑ Fabricate Si thin film solar cell in RJ architecture to promote performance

- ❑ Si nanowire matrix for strong light harvesting
- ❑ Economy in the step of TCO texturing
- ❑ Allowing thinner absorber for higher defect tolerance and stability

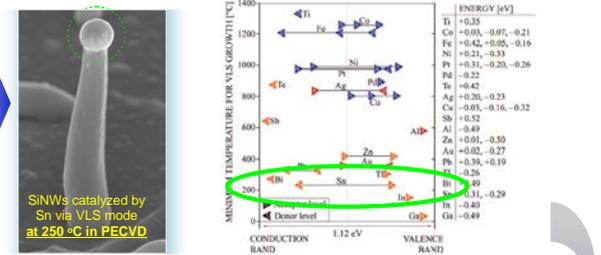
❑ Combine mature & low-cost thin film technology with VLS SiNW growth

- ❑ Vapor-Liquid-Solid (VLS) bottom-up represents a low-cost approach
- ❑ Low temperature and compatible to the standard thin film deposition in PECVD system
- ❑ All-in-situ fabrication: ideally one-pump-down

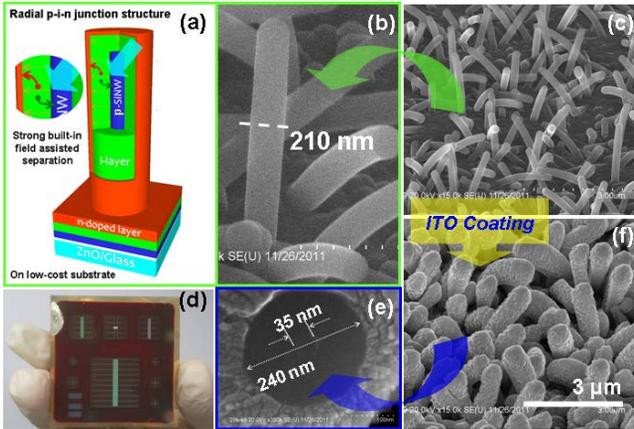


Advantages of using low-melting-point alternatives catalysts:

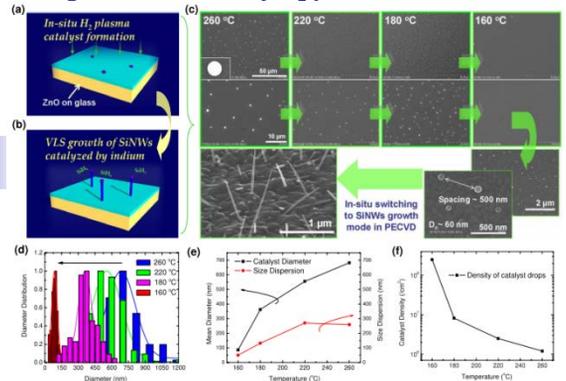
- Low-temperature growth down to 235 °C for Sn and 167 °C for In
- No mid-gap recombination centers, as introduced by Au



[1] Nanotechnology 19, 485605 (2008) [2]. J. of Materials Chemistry, 18, 5187 (2008)
 [3] Applied Physics Letter, 97, 023107 (2010) [4] Applied Physics Letter, 98, 123113 (2011)



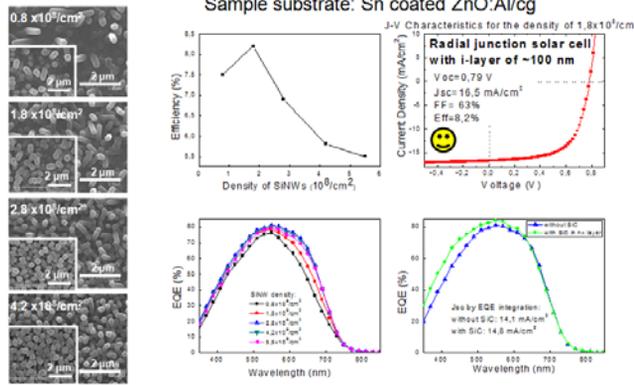
Effective distribution control of catalyst drops on ZnO/glass substrate by H₂ plasma treatment



For details, see L. Yu, et al. *Nanotechnology*, 23, 194011 (2012)

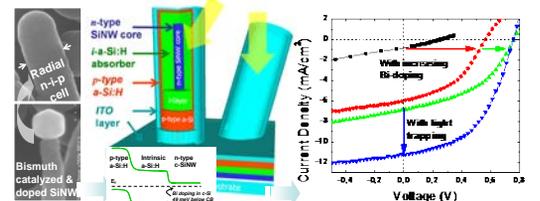
Effect of density variation

Sample substrate: Sn coated ZnO:Al/cg



- > Record efficiency of 8.2% is demonstrated
- > Use of high bandgap SiC in the n+ layer helps to obtain better spectral response in the low wavelength region.

Bismuth-catalyzed & doped Si nanowires for one-pump-down fabrication of radial junction solar cells



- ✓ Demonstrate the Bi-catalyst doping in the SiNW cores for radial junction solar cells, with Voc=0.76 V and high Jsc boosted by strong light trapping effect
- ✓ Exempts the use of toxic phosphine gas, procedure simplification and cost reduction

For details, see L. Yu, et al. *Nano Letters* 12, 4153–4158 (2012)

Conclusions & Perspectives:

- > VLS-grown SiNWs have been explored to build up a new generation of high performance radial junction thin film solar cell.
- > Aiming at a radial single junction cell to > 11%, and > 15 % for radial tandem junction structure.

Other References

[1] Solar Energy Materials & solar cells, 94, 1855 (2010) [2]. Prog. Photovolt: Res. Appl. 10,1002/pip.1245 (2011)
 [3] Nanotechnology, 23, 194011 (2012)